





# **VERTING VOLTAGE DOUBLER**

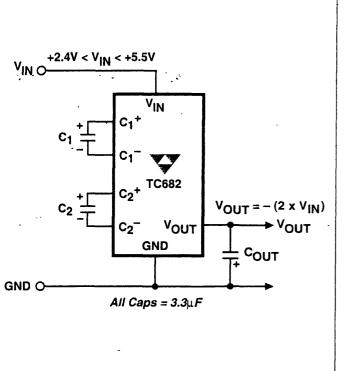
#### **ATURES**

99.9% Voltage Conversion Efficiency
92% Power Conversion Efficiency
Wide Input Voltage Range ......+2.4V to +5.5V
Only 3 External Capacitors Required
185µA Supply Current
Space-Saving 8-Pin SOIC and 8-Pin Plastic DIP
Packages

#### **PLICATIONS**

- 10V from +5V Logic Supply
- 6V from a Single 3V Lithium Cell Portable Handheld Instruments Cellular Phones LCD Display Bias Generator Panel Meters Operational Amplifier Power Supplies

#### PICAL OPERATING CIRCUIT



## **GENERAL DESCRIPTION**

The TC682 is a CMOS charge pump converter that provides an inverted doubled output from a single positive supply. An on-board 12kHz (typical) oscillator provides the clock and only 3 external capacitors are required for full circuit implementation.

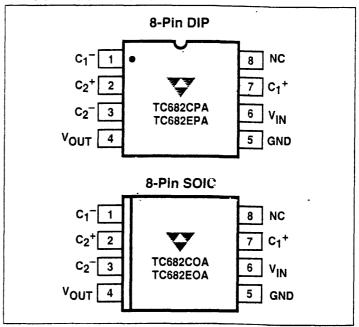
Low output source impedance (typically  $140\Omega$ ), provides output current up to 10mA. The TC682 features low quiescent current and high efficiency, making it the ideal choice for a wide variety of applications that require a negative voltage derived from a single positive supply (for example: generation of -6V from a 3V lithium cell or -10V generated from a +5V logic supply).

The minimum external parts count and small physical size of the TC682 make it useful in many medium-current, dual voltage analog power supplies.

# **ORDERING INFORMATION**

Part No.	Package	Temp. Range		
TC682COA	8-Pin SOIC	0°C to +70°C		
TC682CPA	8-Pin Plastic D <sub>1</sub> P	0°C to +70°C		
TC682EOA	8-Pin SOIC	- 40°C to +85°C		
TC682EPA	8-Pin Plastic DIP	- 40°C to +85°C		
TC7660EV	Evaluation Kit for Charge Pump Family			

#### **PIN CONFIGURATIONS**



TC682-2 8/21/96

# INVERTING VOLTAGE DOUBLER

# **TC682**

# **ABSOLUTE MAXIMUM RATINGS\***

V <sub>IN</sub>	+5.8V
V <sub>IN</sub> dV/dT	
V <sub>OUT</sub>	– 11.6V
Vout Short-Circuit Duration	Continuous
Power Dissipation (T <sub>A</sub> ≤ 70°C)	
Plastic DIP	730mW
SOIC	470mW
Storage Temperature Range	- 65°C to +150°C
Lead Temperature (Soldering, 10 sec)	+300°C

\*This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of the specifications is not implied. Exposure to Absolute Maximum Rating Conditions for extended periods may affect device reliability.

# **ELECTRICAL CHARACTERISTICS:** Over Operating Temperature Range, V<sub>IN</sub> = +5V, test circuit Figure 1, unless otherwise indicated.

Symbol	Parameter	Test Conditions	Min	Тур	Max	Unit
VIN	Supply Voltage Range	$R_L = 2k\Omega$	2.4		5.5	V
I <sub>IN</sub>	Supply Current	R <sub>L</sub> = ∞, T <sub>A</sub> = 25°C R <sub>L</sub> = ∞	_	185	300 400	μΑ
R <sub>OUT</sub>	V <sub>OUT</sub> Source Resistance Source Resistance	I <sub>L</sub> = 10mA, T <sub>A</sub> = 25°C I <sub>L</sub> = 10mA I <sub>L</sub> = 5mA, V <sub>IN</sub> = 2.8V	=	140 — 170	180 230 320	Ω
Fosc	Oscillator Frequency		_	12	_	kHz
PEFF	Power Efficiency	$R_L = 2k\Omega$ , $T_A = 25^{\circ}C$	90	92	-	%
Vout Eff	Voltage Conversion Efficiency	V <sub>OUT</sub> , R <sub>L</sub> = ∞	99	99.9	1 — 1	%

TelCom Semiconductor reserves the right to make changes in the circuitry or specifications detailed in this manual at any time without notice. Minimums and maximums are guaranteed. All other specifications are intended as guidelines only. TelCom Semiconductor assumes no responsibility for the use of any circuits described herein and makes no representations that they are free from patent infringement.

## PIN DESCRIPTION

Pin No. 8-Pin DIP/SOIC	Symbol	Description
1	C <sub>1</sub>	Input. Capacitor C1 negative terminal.
2	C <sub>2</sub>	Input. Capacitor C2 positive terminal.
3	C <sub>2</sub>	Input. Capacitor C2 negative terminal
4	V <sub>OUT</sub>	Output. Negative output voltage (- 2V <sub>IN</sub> )
5	GND	Input. Device ground.
6	ViN	Input. Power supply voltage.
7	Cţ	Input. Capacitor C1 positive terminal
8	N/C	No Connection

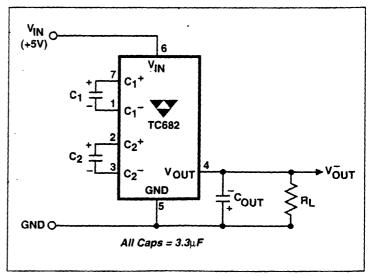


Figure 1. TC682 Test Circuit

#### *AILED DESCRIPTION*

#### \_ 1

s charge storage – before this phase of the clock capacitor  $C_1$  is already charged to +5V.  $C_1^+$  is then ad to ground and the charge in  $C_1^-$  is transferred to  $C_2^-$  :  $C_2^+$  is at +5V, the voltage potential across capacitor ow –10V.

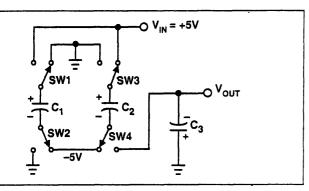


Figure 2. Charge Pump - Phase 1

#### ≥ 2

 $_3$  transfer – phase two of the clock connects the e terminal of  $C_2$  to the negative side of reservoir or  $C_3$  and the positive terminal of  $C_2$  to ground, rring the generated – 10V to  $C_3$ . Simultaneously, the  $_3$  side of capacitor  $C_1$  is switched to  $_4$ 5V and the e side is connected to ground.  $C_2$  is then switched to d GND and Phase 1 begins again.

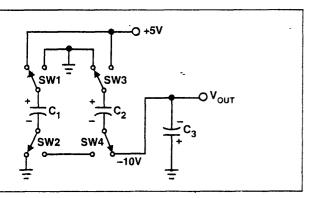


Figure 3. Charge Pump - Phase 2

#### **MUM OPERATING LIMITS**

 $\ni$  TC682 has on-chip zener diodes that clamp  $V_{IN}$  to mately 5.8V, and  $V_{OUT}$  to -11.6V. Never exceed the Im supply voltage or excessive current will be shunted e diodes, potentially damaging the chip. The TC682 rate over the entire operating temperature range with t voltage of 2V to 5.5V.

#### **EFFICIENCY CONSIDERATIONS**

Theoretically a charge pump voltage multiplier can approach 100% efficiency under the following conditions:

- The charge pump switches have virtually no offset and are extremely low on resistance.
- Minimal power is consumed by the drive circuitry
- The impedances of the reservoir and pump capacitors are negligible.

For the TC682, efficiency is as shown below:

$$\begin{aligned} \text{Voltage Efficiency} &= V_{OUT} \, / \, (-\, 2V_{IN}) \\ V_{OUT} &= -\, 2V_{IN} \, + V_{DROP} \\ V_{DROP} &= (I_{OUT}) \, (R_{OUT}) \end{aligned}$$

Power Loss =  $I_{OUT}(V_{DROP})$ 

There will be a substantial voltage difference between  $V_{OUT}^-$  and 2  $V_{IN}^-$  if the impedances of the pump capacitors  $C_1$  and  $C_2$  are high with respect to their respective output loads.

Larger values of reservoir capacitor  $C_3$  will reduce output ripple. Larger values of both pump and reservoir capacitors improve the efficiency. See "Capacitor Selection" in Applications section.

#### **APPLICATIONS**

# **Negative Doubling Converter**

The most common application of the TC682 is as a charge pump voltage converter which provides a negative output of two times a positive input voltage (Figure 4).

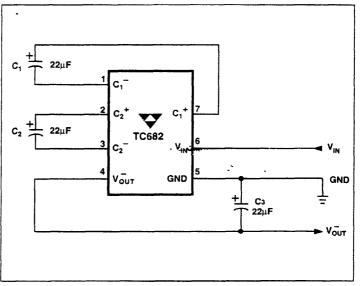


Figure 4. Inverting Voltage Doubler

4

# **Capacitor Selection**

The output resistance of the TC682 is determined, in part, by the ESR of the capacitors used. An expression for Rout is derived as shown below:

$$R_{OUT} = 2(R_{SW1} + R_{SW2} + ESR_{C1} + R_{SW3} + R_{SW4} + ESR_{C2}) + 2(R_{SW1} + R_{SW2} + ESR_{C1} + R_{SW3} + R_{SW4} + ESR_{C2}) + 17(f_{PUMP} \times C1) + †/(f_{PUMP} \times C2) + ESR_{C3}$$

Assuming all switch resistances are approximately equal...

$$R_{OUT} = 16R_{SW} + 4ESR_{C1} + 4ESR_{C2} + ESR_{C3} + 1/(f_{PUMP} \times C1) + 1/(f_{PUMP} \times C2)$$

Rout is typically 140 $\Omega$  at +25°C with  $V_{IN} = +5V$  and 3.3µF low ESR capacitors. The fixed term (16R<sub>SW</sub>) is about  $80-90\Omega$ . It can be seen easily that increasing or decreasing values of C1 and C2 will affect efficiency by changing R<sub>OUT</sub>. However, be careful about ESR. This term can quickly become dominant with large electrolytic capacitors. Table 1 shows  $R_{OUT}$  for various values of C1 and C2 (assume 0.5 $\Omega$ ESR). C1 must be rated at 6VDC or greater while C2 and C3 must be rated at 12VDC or greater.

Output voltage ripple is affected by C3. Typically the larger the value of C3 the less the ripple for a given load current. The formula for P-P VRIPPLE is given below:

$$V_{RIPPLE} = \{1/[2(f_{PUMP} \times C3)] + 2(ESR_{C3})\} (I_{OUT})$$

For a  $10\mu F$  (0.5 $\Omega$  ESR) capacitor for C3,  $f_{PUMP} = 10kHz$ and I<sub>OUT</sub> = 10mA the peak-to-peak ripple voltage at the output will be less then 60mV. In most applications (IOUT < = 10mA) a 10-20μF capacitor and 1-5μF pump capacitors will suffice. Table 2 shows V<sub>RIPPLE</sub> for different values of C3 (assume  $1\Omega$  ESR).

Table 1. Rout vs. C1, C2

R <sub>OUT</sub> (Ω)
4085
2084
510
285
145 -
125
105
94
87

Table 2. VRIPPLE Peak- to-Peak vs. C3 (IOUT = 10mA).

C3 (μF)	V <sub>RIPPLE</sub> (mV)	
0.50	1020	
1.00	520	
3.30	172	
5.0σ	120	
10.00	70	
22.00	43	
100.00	25	

# Paralleling Devices

Paralleling multiple TC682s reduces the output resistance of the converter. The effective output resistance is the output resistance of a single device divided by the number of devices. As illustrated in Figure 5, each requires separate pump capacitors C<sub>1</sub> and C<sub>2</sub>, but all can share a single reservoir capacitor.

# -5V Regulated Supply From A Single 3V Battery

Figure 6 shows a - 5V power supply using one 3V battery. The TC682 provides - 6V at Vout, which is regulated to -5V by the negative LDO. The input to the TC682 can vary from 3V to 5.5V without affecting regulation appreciably. A TC54 device is connected to the battery to detect undervoltage. This unit is set to detect at 2.7V. With higher input voltage, more current can be drawn from the outputs of the TC682. With 5V at V<sub>IN</sub>, 10mA can be drawn from the regulated output. Assuming 150 $\Omega$  source resistance for the converter, with  $l\bar{l} = 10$ mA, the charge pump will droop 1.5V.

Figure 5. Paralleling TC682 for Lower Output Source Resistance

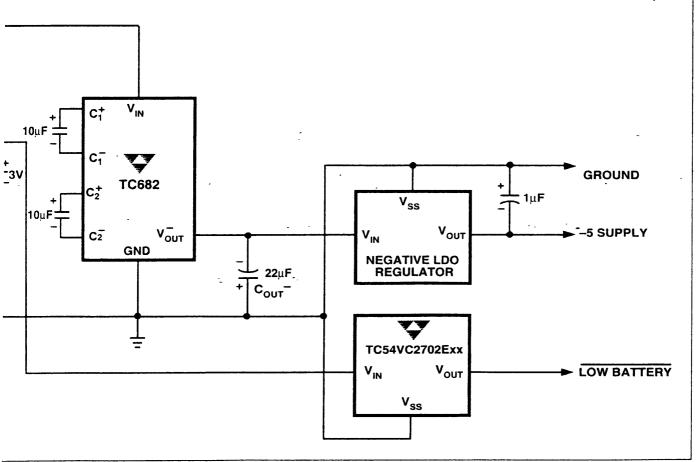


Figure 6. Negative Supply Derived from 3V Battery

1

# TYPICAL CHARACTERISTICS (F<sub>OSC</sub> = 12kHz)

